Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

 (Currently Amended) A quartz ring for use in a plasma processing apparatus, comprising:

an inner perimeter:

a main surface extending outwardly from the inner perimeter;

a first portion around the inner perimeter, the first portion having a flat first region on the main surface and being in direct contact with plasma; and

a second portion adjacent to an outer perimeter of the first portion having a smaller thickness than that of the first portion, the second portion having a second region adjacent to the first region on the main surface, the second region having a height lower than that of the first region, the second portion extending outwardly from the outer perimeter of the first portion to the an outer perimeter of the quartz ring;

wherein the first region and the second region are regions of the quartz ring and are parallel to each other, wherein the first portion and the second portion are of a monolithic piece of the quartz ring, and wherein the quartz ring surrounds a wafer holder.

- (Previously Presented) The quartz ring according to claim 1, wherein the second region is flat and is parallel to the first region.
- (Previously Presented) The quartz ring according to claim 1, further comprising a flat second surface opposite to the main surface, the second surface being parallel to the first region.
- 4. (Previously Presented) The quartz ring according to claim 1, wherein a difference of the heights of the first region and the second region is about 0.1 mm to about 2 mm.

- (Previously Presented) The quartz ring according to claim 1, further comprising a second surface opposite to the main surface, the second surface having a beveled portion along the inner perimeter.
- (Currently Amended) A plasma processing apparatus, comprising:

 a processing chamber to accommodate a workpiece to be processed;
 an electrode within the processing chamber to generate a plasma, the electrode having an outer perimeter; and
 - a quartz ring that surrounds the outer perimeter of the electrode, comprising:
 an inner perimeter;
 - a main surface extending outwardly from the inner perimeter;
- a first portion around the inner perimeter, the first portion having a flat first region on the main surface and being in direct contact with plasma; and

a second portion adjacent to an outer perimeter of the first portion having a smaller thickness than that of the first portion, the second portion having a second region adjacent to the first region on the main surface, the second region having a height lower than that of the first region extending outwardly from the outer perimeter of the first portion to the outer perimeter of the quartz ring;

wherein the first region and the second region are regions of the quartz ring and are parallel to each other, wherein the first portion and the second portion are of a monolithic piece of the quartz ring, and wherein the quartz ring surrounds a wafer holder.

- 7. (Previously Presented) The apparatus according to claim 6, wherein: the outer perimeter of the electrode has a side surface; and the inner perimeter of the quartz ring has a side surface that faces the side surface of the outer perimeter of the electrode.
- 8. (Previously Presented) The apparatus according to claim 6, wherein: the workpiece to be processed is mounted on the electrode; and a height of the first region of the quartz ring is substantially the same as that of a surface of the workpiece mounted on the electrode.
- 9. (Previously Presented) The apparatus according to claim 6, further comprising a second quartz ring having a second main surface, the second main surface faces the first region of the quartz ring to form a gap between them,

wherein a difference between the heights of the first region and the second region of the quartz ring is not substantially larger than the gap.

10-25. (Canceled)